

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

GATE ELECTRODE FORMING METHODS USING
CONDUCTIVE HARD MASK

Application Number :

Confirmation Number:

First Named Applicant: Oleg Gluschenkov

Attorney Docket Number: FIS920040196US1

Art Unit:

Examiner:

Search string: (6693333 or 6664153 or 6633497 or 6448590 or 6441447 or 6426301 or 6204073
or 20030109121 or 20030153139 or 20020196647 or 20020177279 or
20030104663).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
WLL	1	6693333	2004-02-17	YU			
WLL	2	6664153	2003-12-16	ANG, ET AL.			
WLL	3	6633497	2003-10-14	NICKEL			
WLL	4	6448590	2002-09-10	ADKISSON, ET AL.			
WLL	5	6441447	2002-08-27	CZAGAS, ET AL.			
WLL	6	6426301	2002-07-30	SHIELDS, ET AL.			
WLL	7	6204073	2001-03-20	NANDAKUMAR, ET AL.			

US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
WLL	1	20030109121	2003-06-05	ROTONDARO			
WLL	2	20030153139	2003-08-14	ANG, ET AL.			
WLL	3	20020196647	2002-12-26	NICKEL			
WLL	4	20020177279	2002-11-28	ADKISSON, ET AL.			

WLL

6/24/2005

W4	5	20030104663	2003-06-05	VISOKAY, ET AL.	1	1	1
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Signature

Examiner Name	Date
<i>Walter L. Smith</i>	<i>6/29/2005</i>

(Use several sheets if necessary)

SERIAL NO. 10/711,642

FILING **9/29/04**

GROUP

[illegible][illegible]

WU			PARK, D.-G., et al., "Thermally Robust Dual-Work Function ALD-Mn _x MOSFETs Using Conventional CMOS Process Flow," 2004 Symposium on VLSI Technology, Digest of Technical Papers, pp. 186-187.

DATE CONSIDERED

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